

## Supplementary

### Role of electron and hole doping in $\text{NdNi}_{1-x}\text{V}_x\text{O}_3$ Nanostructure

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Sample  $S_3$  and  $S_4$  were synthesized with higher doping concentration of V. The EDX data confirms that V mostly replaces Ni ion as  $\text{NdNi}_{1-x}\text{V}_x\text{O}_3$  ( $x \sim 0.025$  for  $S_3$  and  $\sim 0.04$  for  $S_4$ ).

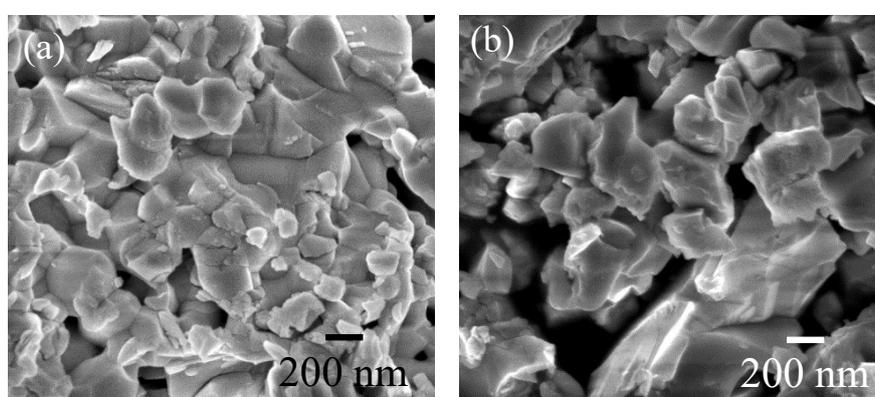


Fig. S1 FESEM images for the pristine samples  $S_3$ , and  $S_4$

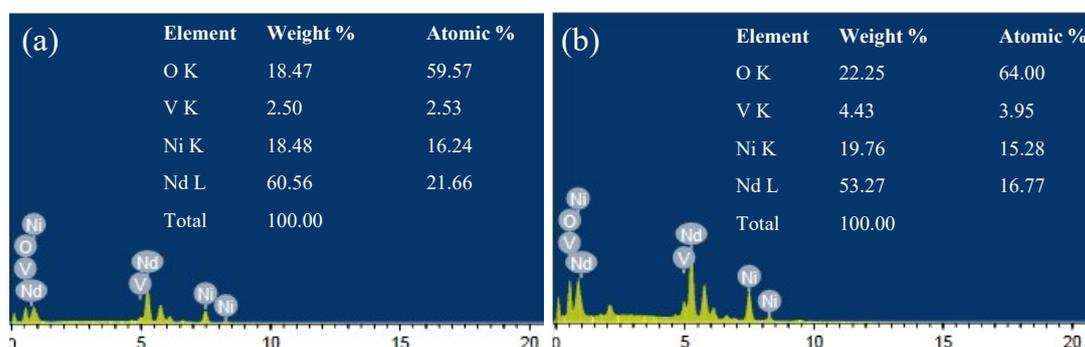


Fig. S2 EDX spectra for the samples  $S_3$  and  $S_4$ . Insets show the elemental composition of each sample with corresponding atomic percentages.

We have performed the X-ray photoelectron spectroscopic (XPS) technique in an ultra-high vacuum (UHV) chamber (Omicron Nanotechnology, of base pressure  $\sim 1.5 \times 10^{-9}$  mbar). The UHV system was equipped with an EA125 hemispherical energy analyser along with a monochromatic X-ray light source (Al  $K\alpha$  of photon energy 1486.6 eV). All the data were collected keeping the samples at room temperature.

The upper panel of figure S3 shows the XPS peaks correspond to Nd3d, Ni2p and O1s transitions.

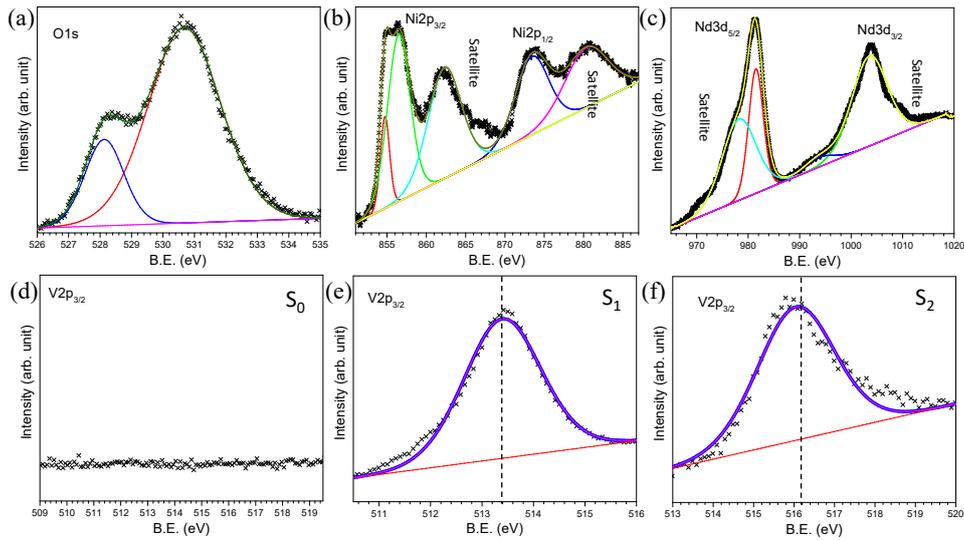


Fig. S3 High resolution XPS spectra of the sample  $S_0$ ,  $S_1$ , and  $S_2$  with corresponding electronic transition of different elements.

The O1s region (figure S3a) shows peaks around 528.3 and 531 eV which can be ascribed to the sample and surface contamination, respectively [R1]. Figure S3b shows the Ni $2p_{3/2}$  peak  $\sim$ 856 eV and Ni $2p_{1/2}$  peak  $\sim$ 873 eV, which corresponds to trivalent Ni [R2]. We also observed characteristic satellites at about 862 and 880 eV. The Nd3d level spectra (figure S3c) shows peaks  $\sim$ 882 and 1004 eV correspond to Nd $3d_{5/2}$  and Nd $3d_{3/2}$  transitions, respectively. We were also able to observe the low binding energy satellites, which is the characteristic feature of Nd multiplet [R3]. For all the three samples we observe similar spectra for Nd, Ni, and O. However, the position of V lines varies for samples  $S_1$ , and  $S_2$ . The lower panel of figure S3 displays the existence of V and its corresponding valence state. Sample  $S_1$  and  $S_2$  confirms the presence of Vanadium, whereas for sample  $S_0$ , no trace of V is observed (figure S3d). The V  $2p_{3/2}$  peak is observed  $\sim$  513.4 eV for sample  $S_1$ , whereas the same is observed  $\sim$  516.2 eV for sample  $S_2$  (figure S3e-f). The position of V  $2p_{3/2}$  peak confirms that V is in +2 state [R4] in sample  $S_1$ , where as it is in +4 state [R5] in sample  $S_2$ , as also argued from resistivity, Raman spectroscopic and XRD analysis.

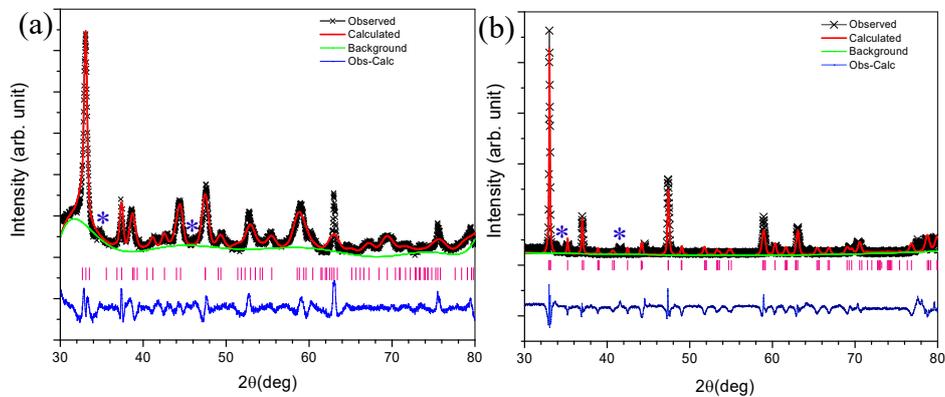


Fig. S4 Rietveld refined X-ray diffraction pattern of samples (a)  $S_3$ , (b)  $S_4$ . Impurity peaks are marked by ‘\*’ sign.

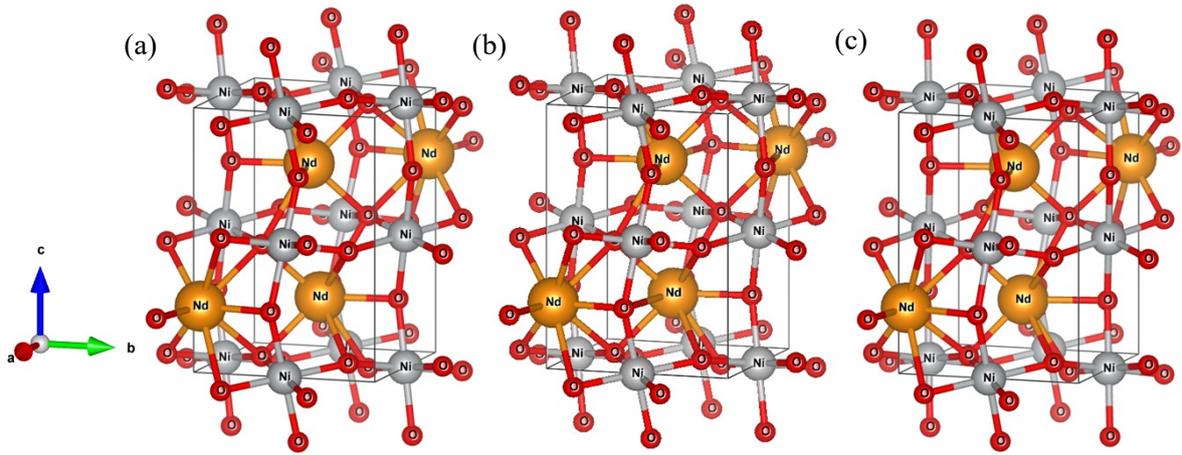


Fig. S5 Schematic structure of  $\text{NdNi}_{1-x}\text{V}_x\text{O}_3$  unit cell of sample (a)  $S_0$  ( $x=0.0$ ), (b)  $S_1$  ( $x=0.1$ ), and (c)  $S_2$  ( $x=0.2$ ), drawn using VESTA software.

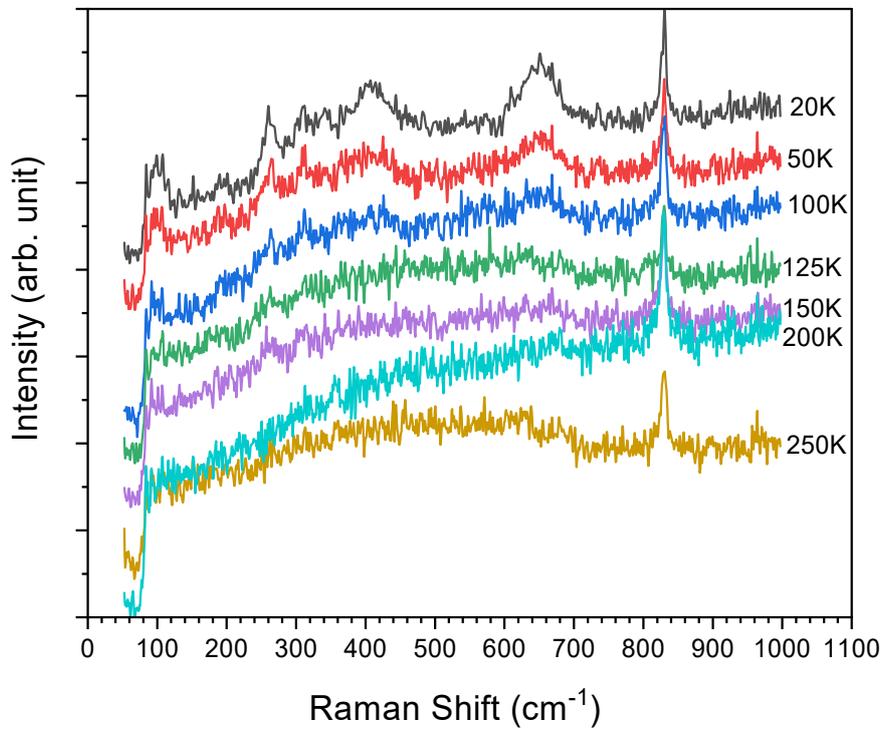


Fig. S6 Raman spectra as a function of temperature for  $\text{NdNi}_{1-x}\text{V}_x\text{O}_3$  ( $x = 0.01$ ) nanostructure (sample  $S_1$ )

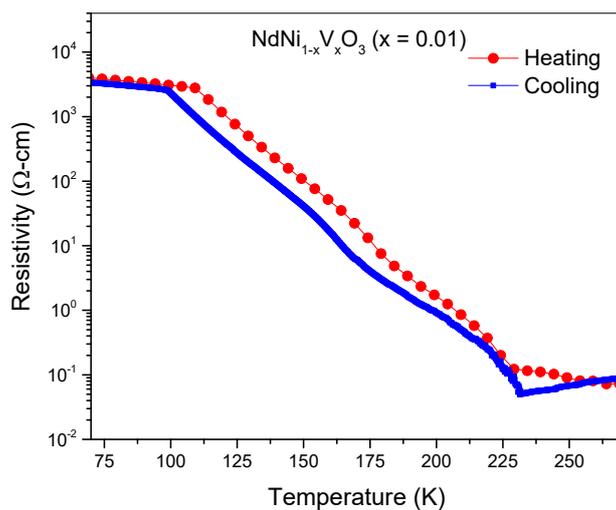


Figure S7. Resistivity plots as a function of temperature for NdNi<sub>1-x</sub>V<sub>x</sub>O<sub>3</sub> (x = 0.01) nanostructure for both heating and cooling cycle with a hysteresis ~ 10 K.

## REFERENCES

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